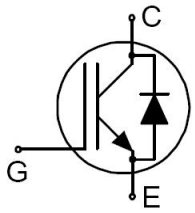
600V , 6A , Trench-FS IGBT

Features

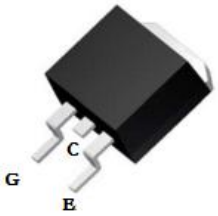
- Advanced Trench+FS (Field Stop) IGBT technology
- Low Collector-Emitter Saturation voltage, typical data is 2.1V @ 6A.
- Easy parallel switching capability due to positive Temperature coefficient in Vce.
- 10uS Short-Circuit
- Fast switching
- High input impedance
- Pb- Free product



Schematic Diagram

Applications

- Home applications
- Intelligent power module.



D2pak

Electrical characteristics(TJ = 25°C unless otherwise noted)						
Symbol	**Parameter**	**Test conditions**	**Units**	**Min.**	**Typ.**	**Max.**
$V_{(BR)CES}$	Collector - Emitter breakdown voltage	V_{GE} = 0V, I_D =250uA	V	600	—	—
$V_{CE(sat)}$	Collector-Emitter Saturation voltage	V_{GE}=15V, I_C=6A,T_C=25°C	V	—	2.1	2.4
		V_{GE}=15V, I_C=6A,T_C=150°C	V	—	2.3	—
$V_{GE(th)}$	Gate threshold voltage	V_{GE}= V_{CE}, I_c = 0.25mA	V	4.0	5.4	6.5
V_F	Diode forward voltage	I_F=6A,T_C=25°C	V	—	1.7	2.1
		I_F=6A,T_C=150°C	V	—	1.3	—
I_{GES}	Gate to Emitter Forward Leakage	Vge=+30V	nA	—	—	200
I_{GESR}	Gate to Emitter reverse Leakage	Vge=-30V		-200	—	—
I_{CES}	Zero gate voltage collector current	V_{CE} =600V	uA	—	—	25